### **Analog Power**

#### AM3405P

## P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low r<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature TSOP-6 Surface Mount Package Saves Board Space
- High power and current handling capability

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> m(Ω)	I <sub>D</sub> (A)	
	$56 @ V_{GS} = -4.5V$	-4.9	
-20	$80 @ V_{GS} = -2.5V$	-4.2	
	$150 @ V_{GS} = -1.8V$	-3.1	





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		V <sub>DS</sub>	-20	V		
Gate-Source Voltage		V <sub>GS</sub>	±12	v		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I_	-4.9			
	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	чD	-4.0	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	±20			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	-1.7	А		
Dower Dissinction <sup>4</sup>	T <sub>A</sub> =25°C	D	2.0	W		
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1 D	1.3			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
	$t \le 5 \text{ sec}$ $R_{\theta J}$	D	62.5	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>		κ <sub>θJA</sub>	110	°C/W	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Symbol	Test Conditions	Limits			Unit
r ar ameter	Symbol	Test Conditions	Min	Тур	Max	Omt
Static						
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-0.7			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	uA
Zero Gate Voltage Drain Current		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -4.5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15			Α
		$V_{GS} = -4.5 \text{ V}, I_D = -4.9 \text{ A}$			56	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -4.2 \text{ A}$			80	mΩ
		$V_{GS} = -1.8 \text{ V}, I_D = -3.1 \text{ A}$			150	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{\rm DS} = -10 \text{ V}, \text{ I}_{\rm D} = -4.9 \text{ A}$		11		S
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S} = 1.7$ A, $V_{\rm GS} = 0$ V		-0.8		V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = -10 V, V_{GS} = -4.5 V,$		8		
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS} = -10$ V, $V_{\rm GS} = -4.5$ V, $I_{\rm D} = -4.9$ A		1.8		nC
Gate-Drain Charge	Q <sub>gd</sub>	$I_{\rm D}$ = -4.9 A		1.9		
Turn-On Delay Time	t <sub>d(on)</sub>			22		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 6 \Omega$ , $I_D = -1 \text{ A},$		35		nS
Turn-Off Delay Time	t <sub>d(off)</sub>	VGEN = -4.5 V		45		no
Fall-Time	t <sub>f</sub>			25		

Notes

- a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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# Typical Electrical Characteristics



Figure 7. Source-Drain Diode Forward Voltage



Figure 9. Vth Gate to Source Voltage Vs Temperature



Figure 8. On-Resistance with Gate to Source Voltage



Figure 10. Single Pulse Maximum Power Dissipation





